|     | 1 A A A A A A A A A A A A A A A A A A A |
|-----|---|
| ΡΛΝ | JIT                                     |
|     | SEMI                                    |
|     | CONDUCTOR                               |

### 60V N-Channel Enhancement Mode MOSFET

Current

#### Features

Voltage

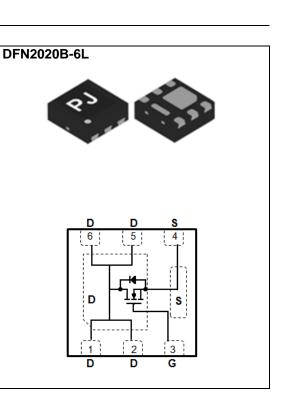
• RDS(ON) , VGS@10V, ID@3.2A<75mΩ

60 V

- Rds(on) , Vgs@4.5V, Id@2.0A<90m $\Omega$
- Advanced Trench Process Technology
- High density cell design for ultra low on-resistance
- AEC-Q101 qualified
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 standard

#### **Mechanical Data**

- Case : DFN2020B-6L Package
- Terminals : Solderable per MIL-STD-750, Method 2026
- Approx. Weight : 0.0003 ounces, 0.0086 grams



### Maximum Ratings and Thermal Characteristics (T<sub>A</sub>=25°C unless otherwise noted)

3.2A

| PARAMETER   |                      | SYMBOL          | LIMIT       | UNITS |
|---|----------------------|-----------------|-------------|-------|
| Drain-Source Voltage  |                      | V <sub>DS</sub> | 60          | V     |
| Gate-Source Voltage   |                      | V <sub>GS</sub> | <u>+</u> 20 | V     |
| Continuous Drain Current  |                      | lь              | 3.2         | А     |
| Pulsed Drain Current  |                      | ldм             | 12.8        | А     |
| Power Dissipation   | T <sub>a</sub> =25°C | PD              | 2.4         | W     |
|   | Derate above 25°C    |                 | 16          | mW/∘C |
| Operating Junction and Storage Temperature Range                    |                      | Tյ,Tsтg         | -55~175     | °C    |
| Typical Thermal Resistance<br>- Junction to Ambient, t<10s (Note 3) |                      | Reja            | 62.5        | °C/W  |



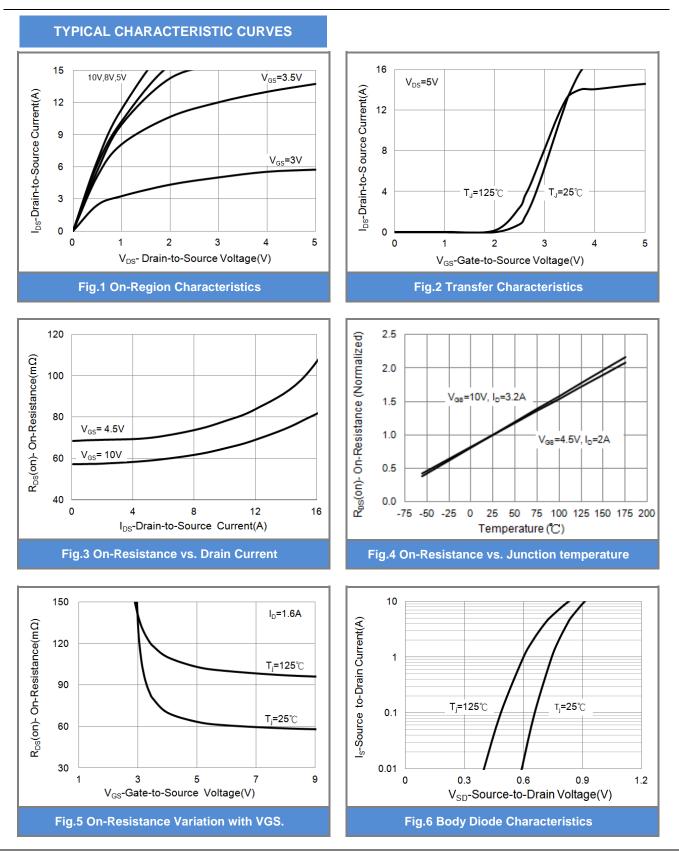
#### Electrical Characteristics (T<sub>A</sub>=25°C unless otherwise noted)

| PARAMETER                        | SYMBOL              | TEST CONDITION  | MIN. | TYP. | MAX.         | UNITS |
|----------------------------------|---------------------|---|------|------|--------------|-------|
| Static                           |                     |   |      |      |              |       |
| Drain-Source Breakdown Voltage   | BV <sub>DSS</sub>   | V <sub>GS</sub> =0V, I <sub>D</sub> =250uA  | 60   | -    | -            | V     |
| Gate Threshold Voltage           | V <sub>GS(th)</sub> | V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250uA                                  | 1.0  | 1.8  | 2.5          | V     |
| Drain-Source On-State Resistance | RDS(on)             | V <sub>GS</sub> =10V, I <sub>D</sub> =3.2A  | -    | 53   | 75           |       |
|                                  |                     | Vgs=4.5V, Id=2.0A   | -    | 61   | 90           | mΩ    |
| Zero Gate Voltage Drain Current  | IDSS                | V <sub>DS</sub> =48V, V <sub>GS</sub> =0V   | -    | -    | 1            | uA    |
| Gate-Source Leakage Current      | lgss                | V <sub>GS</sub> = <u>+</u> 20V, V <sub>DS</sub> =0V                                       | -    | -    | <u>+</u> 100 | nA    |
| Dynamic (Note 6)                 |                     |   |      |      |              |       |
| Total Gate Charge                | Qg                  | V <sub>DS</sub> =48V, I <sub>D</sub> =3.0A,<br>V <sub>GS</sub> =10V <sup>(Note 1,2)</sup> | -    | 9.3  | -            | nC    |
| Gate-Source Charge               | $Q_{gs}$            |   | -    | 2.2  | -            |       |
| Gate-Drain Charge                | $Q_{gd}$            | VGS=10V (1000 1,2)  | -    | 1.9  | -            |       |
| Input Capacitance                | Ciss                |   | -    | 509  | -            | pF    |
| Output Capacitance               | Coss                | V <sub>DS</sub> =15V, V <sub>GS</sub> =0V,<br>f=1.0MHZ                                    | -    | 47   | -            |       |
| Reverse Transfer Capacitance     | Crss                |   | -    | 23   | -            |       |
| Turn-On Delay Time               | td <sub>(on)</sub>  | $V_{DD}=30V, I_{D}=3.0A,$<br>$V_{GS}=10V,$<br>$R_{G}=3.3\Omega$ (Note 1,2)                | -    | 3.2  | -            |       |
| Turn-On Rise Time                | tr                  |   | -    | 9.7  | -            |       |
| Turn-Off Delay Time              | td <sub>(off)</sub> |   | -    | 18.5 | -            | ns    |
| Turn-Off Fall Time               | tf                  | RG=3.312 (1000 1)=)   | -    | 6.4  | -            |       |
| Drain-Source Diode               |                     |   |      | •    | -            |       |
| Maximum Continuous Drain-Source  | ls                  |   |      | _    | 3.2          | Α     |
| Diode Forward Current            | 15                  |   | -    | -    | 3.2          | ~     |
| Diode Forward Voltage            | V <sub>SD</sub>     | Is=1A, V <sub>GS</sub> =0V  | -    | 0.75 | 1.2          | V     |

NOTES :

- 1. Pulse width
- 2. Essentially independent of operating temperature typical characteristics.
- 3. The maximum current rating is package limited.
- 4. Repetitive rating, pulse width limited by junction temperature TJ(MAX)=150°C. Ratings are based on low frequency and duty cycles to keep initial TJ =25°C.
- 5. R<sub>®JA</sub> is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch<sup>2</sup> with 2oz.square pad of copper.
- 6. Guaranteed by design, not subject to production testing.







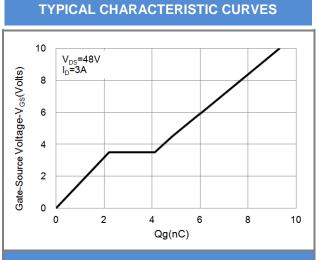
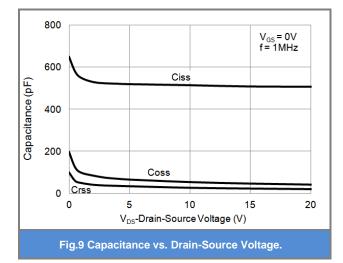


Fig.7 Gate-Charge Characteristics



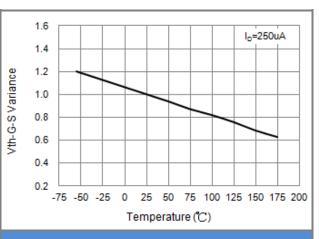


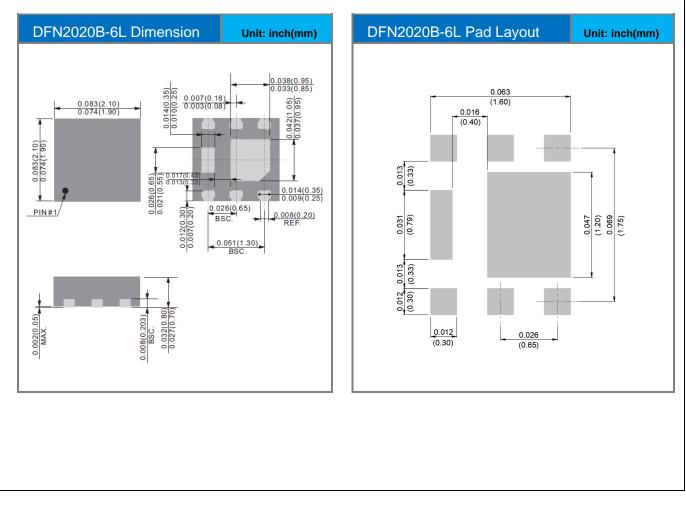
Fig.8 Threshold Voltage Variation with Temperature.



### **Product and Packing Information**

| Part N  | o. Packa | age Type Pac | cking Type    | Marking |
|---------|----------|--------------|---------------|---------|
| PJQ2460 | -AU DFN2 | 2020B-6L 3K  | pcs / 7" reel | 460     |

### Packaging Information & Mounting Pad Layout





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